Structure Controlled Synthesis of Single-Walled Carbon Nanotubes Using Solution Based Catalyst Deposition

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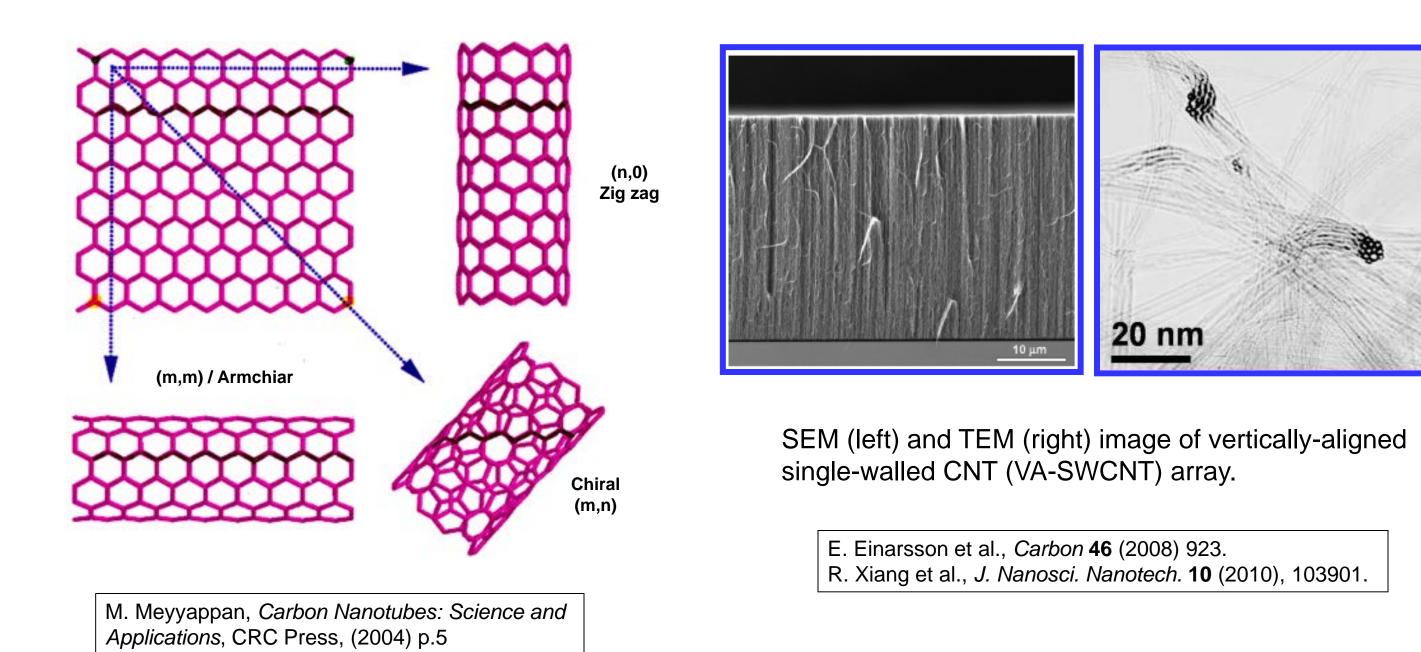
Because of its excellent electrical, optical, mechanical and physical properties, single-walled carbon nanotube (SWCNT) has been considered for many applications. We would like to exploit the unique electronic properties of SWCNTs that arise from their structural parameters such as diameter and chirality. Unfortunately, the large-scale synthesis of SWCNTs with predetermined diameter and chirality is a major challenge because of their structure dependence. We address this problem by studying the scalable tailored structure controlled synthesis of SWCNTs through thermal chemical vapor deposition (CVD). Our process uses ethylene the carbon source in the presence of water. By varying the concentration of Fe catalyst, we synthesized SWCNT array film with different thickness ranging from the nanometer to the millimeter scale. We also demonstrate a simple process to control the diameter of SWCNTs. The results from this study can be used to apply for nano-scale-electronic devices, mechanical application, etc.





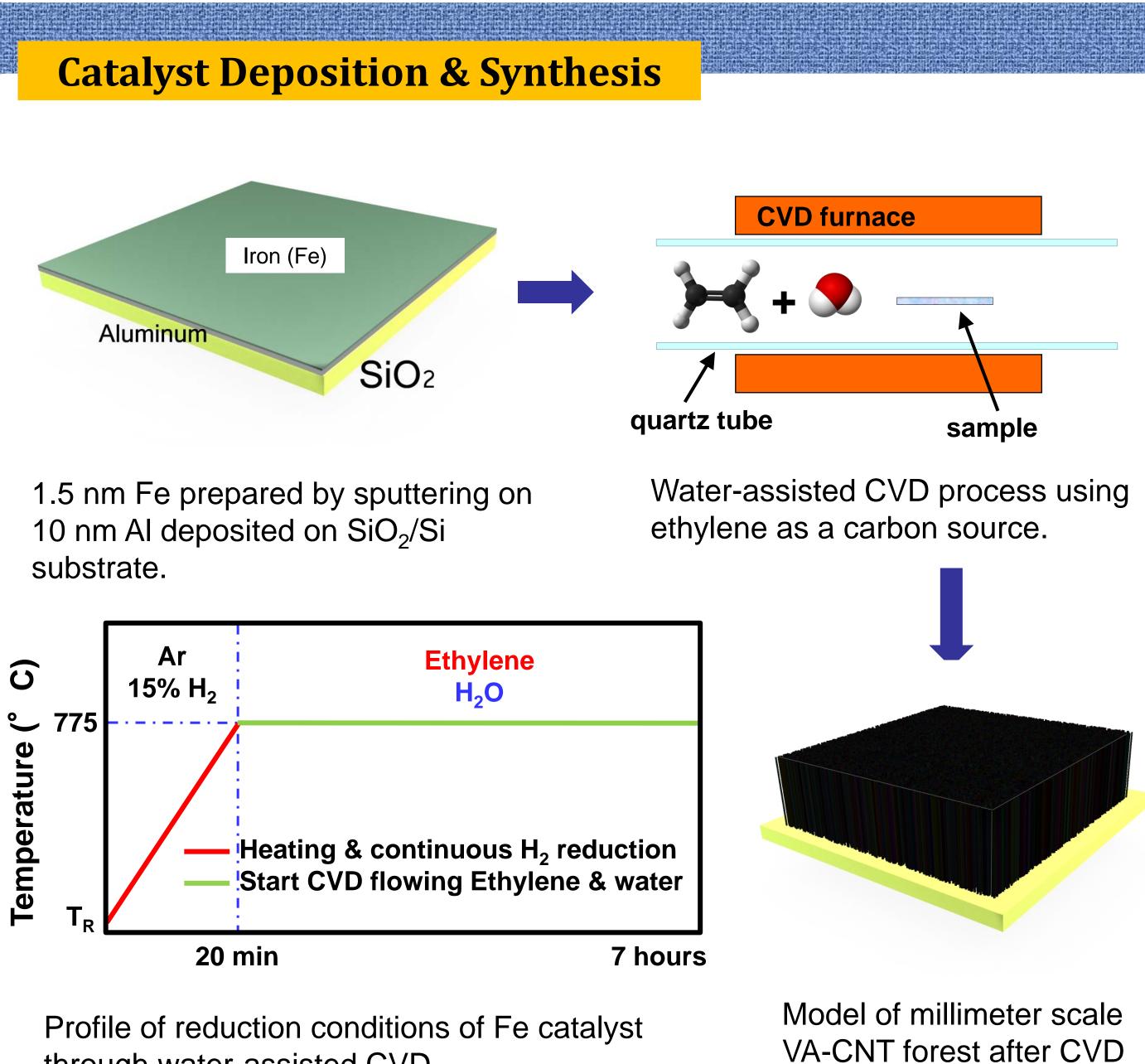
What Is Carbon Nanotube (CNT) ?

 \succ CNT is formed by rolling up a graphene sheet characterized by its chirality. Many properties are chirality dependent.



Why is structure control needed?

Producing uniform structure with nearly homogenous properties. >Inducing to many more potential applications such as mechanical and electrical properties.



process.

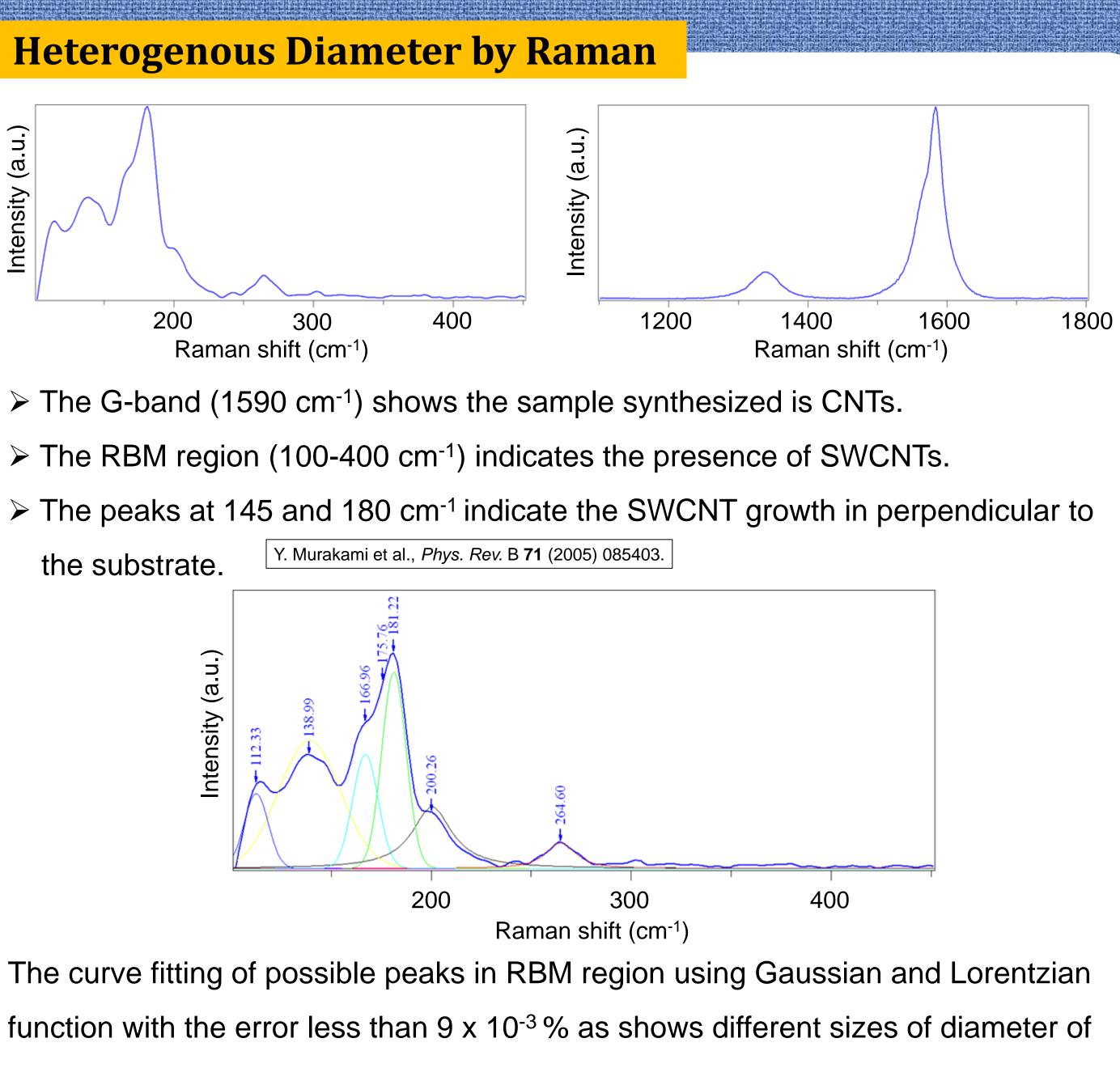
through water-assisted CVD.

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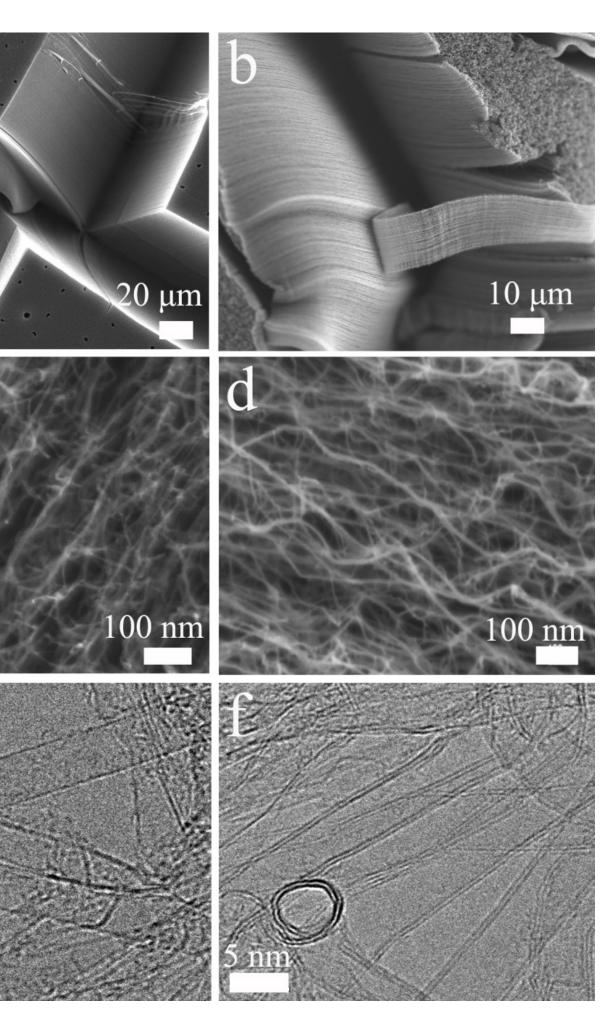
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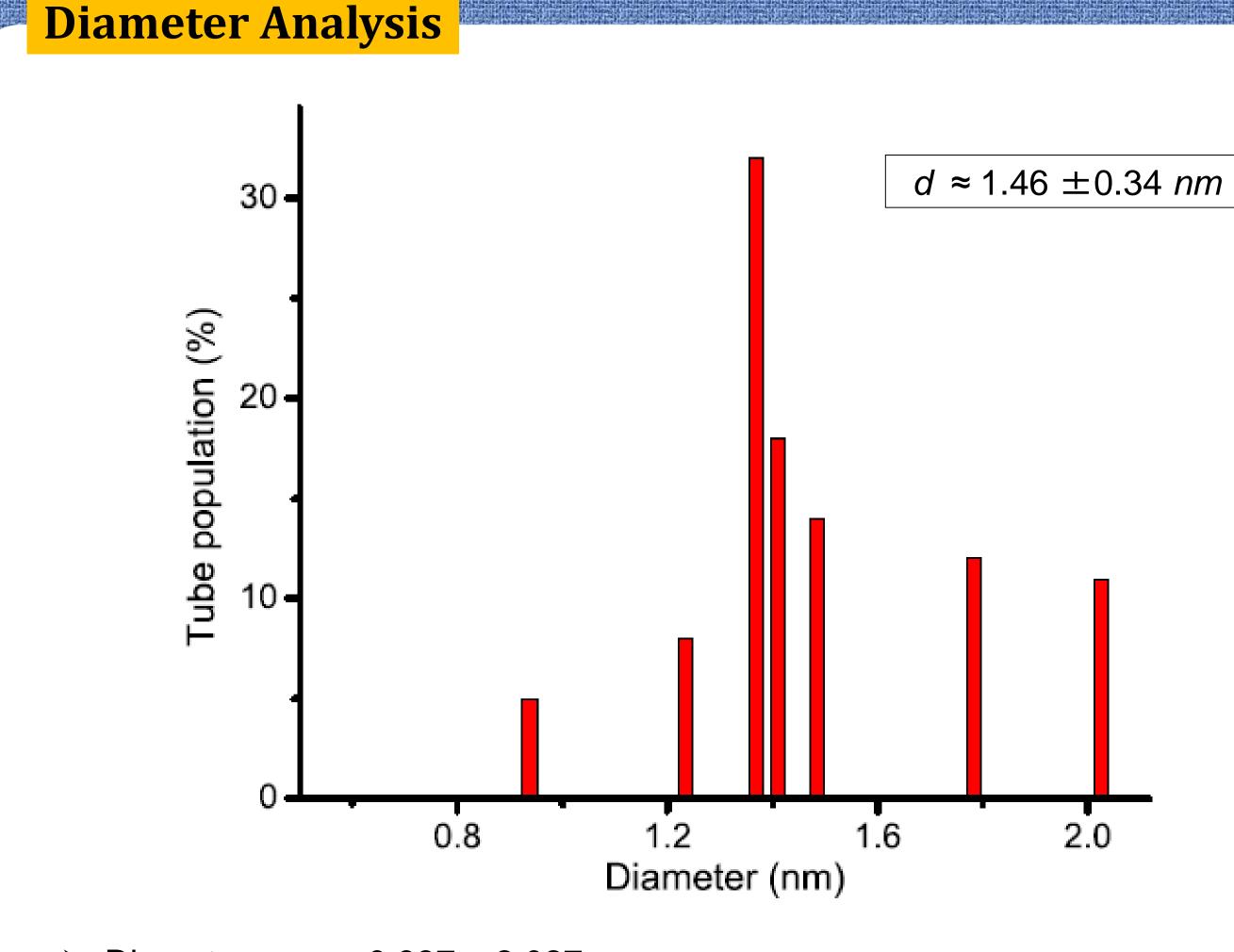
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Vertically-Aligned Carbon Nanotubes (VA-CNTs) Photographs of millimeter scale VA-CNT forest grown by waterassisted ethylene CVD. **VA-CNT** forest VA-CNT forest (~1 cm (1.4 mm/h) SEM micrographs of CNT forest (a-d) show dense morphology of CNTs and well aligned along tubes, and the tube diameter investigated by TEM images (e,f) indicates few-walled CNTs with diameter control. **Heterogenous Diameter by Raman** 1200 400 1400 200 Raman shift (cm⁻¹) \succ The G-band (1590 cm⁻¹) shows the sample synthesized is CNTs. sample \succ The RBM region (100-400 cm⁻¹) indicates the presence of SWCNTs. \succ The peaks at 145 and 180 cm⁻¹ indicate the SWCNT growth in perpendicular to Y. Murakami et al., *Phys. Rev.* B **71** (2005) 085403. the substrate.



SWCNTs in the sample.





- Diameter range: 0.937 2.027 nm
- Mean diameter: 1.368 nm (Population: 32%)

Summary

- diameter control of few-walled CNT.

Further Works

References

- 2. E. Einarsson et al., *Carbon* **46** (2008) 923.
- 4. Y. Murakami et al., *Phys. Rev.* B **71** (2005) 085403.

Acknowledgement



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➤ Major 3 diameters: 1.368, 1.411 and 1.485 nm (64%)

> Not only large scale production of CNTs, but also structure and diameter control

> Millimeter scale VA-CNT forest can be achieved by water assistance (~1 cm). \succ Water and aluminum can promote large scale growth.

> Aluminum layer was used to restrict the aggregation Fe catalyst, resulting in

> To achieve large scale high purity SWCNT forest. \succ Further applications such as gas sensor, reinforce formation, H₂ storage, *etc*.

M. Meyyappan, Carbon Nanotubes: Science and Applications, CRC Press, (2004) p.5. 3. R. Xiang et al., *J. Nanosci. Nanotech.* **10** (2010), 103901.

